

Serial No.: 10796,704

Examiner: Delma R. Flores Ruiz

Title: SEMICONDUCTOR LASER DEVICE AND OPTICAL PICK UP APPARATUS USING THE SAME

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Amendments to the Claims:

This listing of claims will replace all prior versions, and listing, of claims in the application.

1-5. (Canceled)

6. (Currently amended) A The-semiconductor laser device according to claim 1, formed on a tilted substrate composed of a compound semiconductor, comprising an active layer and two cladding layers interposing the active layer therebetween, wherein one of the cladding layers forms a mesa-shaped ridge, the ridge includes a first region where a width of a bottom portion of the ridge is substantially constant along an optical path direction, and a second region where the width of the bottom portion of the ridge is varied continuously in the optical path direction, the second region is placed between the first region and an end face in an optical path, and wherein, at a boundary between the first region and the second region, the width of the bottom portion of the ridge in the first region is substantially the same as that in the second region.

7. (Currently amended) A The-semiconductor laser device according to claim 1, formed on a tilted substrate composed of a compound semiconductor, comprising an active layer and two cladding layers interposing the active layer therebetween, wherein one of the cladding layers forms a mesa-shaped ridge, the ridge includes a first region where a width of a bottom portion of the ridge is substantially constant along an optical path direction, and a second region where the width of the bottom portion of the ridge is varied continuously in the optical path direction, the second region is placed between the first region and an end face in an optical path, and

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~~wherein~~ a difference between the width of the bottom portion of the ridge in the first region and a maximum value of the width of the bottom portion of the ridge in the second region is 0.5 μm or less.

8-15. (Canceled)

16. (Currently amended) ~~A~~ The semiconductor laser device according to claim 1, formed on a tilted substrate composed of a compound semiconductor, comprising an active layer and two cladding layers interposing the active layer therebetween,

wherein one of the cladding layers forms a mesa-shaped ridge,

the ridge includes a first region where a width of a bottom portion of the ridge is substantially constant along an optical path direction, and a second region where the width of the bottom portion of the ridge is varied continuously in the optical path direction,

the second region is placed between the first region and an end face in an optical path, and

~~wherein~~ a length of the first region is 10% to 50% with respect to a resonator length.